

## **AMENDMENTS TO THE SPECIFICATION:**

Please amend the specification as follows:

**Please amend the first full paragraph on page 8 of the specification as follows:**

First, the wafer W is placed on the lower electrode 106, the temperature of which has been adjusted to a specific level in advance and ~~the temperature of the wafer W is sustained within a range of approximately 20°C ~ 50°C in correspondence to the particulars of the processing. For instance, the temperature at the bottoms of the contact holes is sustained at approximately 20°C, the temperature at the openings is sustained at approximately 30°C and the temperature at the sidewalls is sustained at approximately 50°C.~~ In addition, vacuum drawing is implemented inside the processing chamber 104 to ensure that the atmosphere inside the processing chamber 104 achieves a specific pressure suitable for the processing, e.g., approximately 20mTorr (2.67 Pa).

**Please amend the last paragraph on page 10 of the specification as follows:**

First, the wafer W is placed on the lower electrode 106, the temperature of which has been adjusted to a specific level in advance and ~~the temperature of the wafer W is sustained within a range of approximately 20°C ~ 50°C in correspondence to the particulars of the processing. For instance, the temperature at the bottoms of the contact holes is sustained at approximately 20°C, the temperature at the openings is sustained at approximately 30°C and the temperature at the sidewalls is sustained at approximately 50°C.~~ In addition, In addition, vacuum drawing is implemented inside

the processing chamber 104 to ensure that the atmosphere inside the processing chamber 104 achieves a specific pressure suitable for the processing, e.g., approximately 20mTorr (2.67 Pa), as in the first embodiment.